
Enhanced EUV Lighting with Optimized C-beam Irradiation

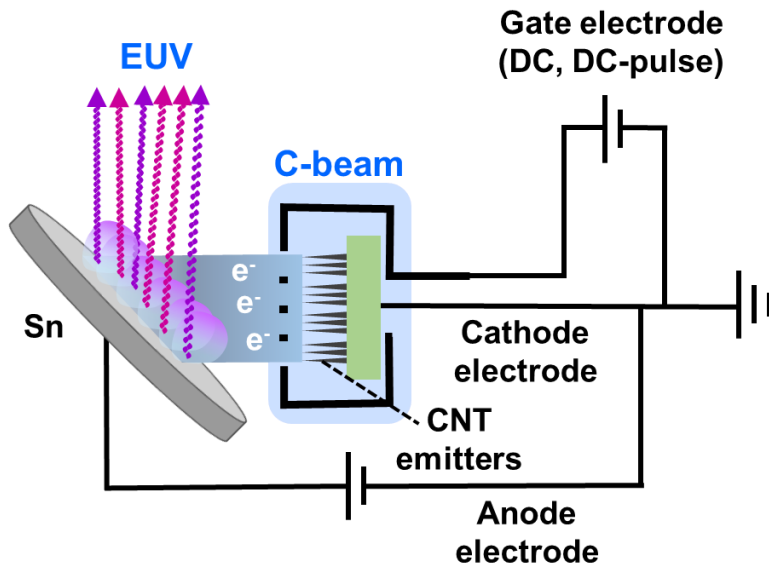
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Schematic of EUV generation with C-beam

Technologies for enhanced EUV lighting

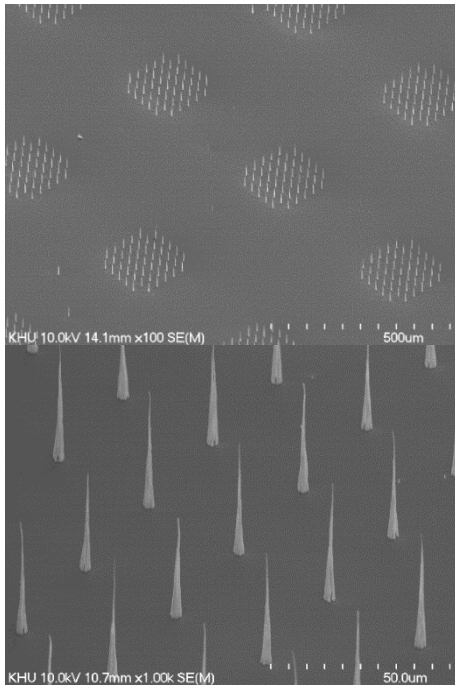
1. Multiple C-beam irradiations
2. Minimal debris technique
3. Using DC-pulse driving
4. Focused C-beam irradiation
5. Etc.

- Among several technologies to enhance EUV lighting, we discuss multiple C-beam irradiations.

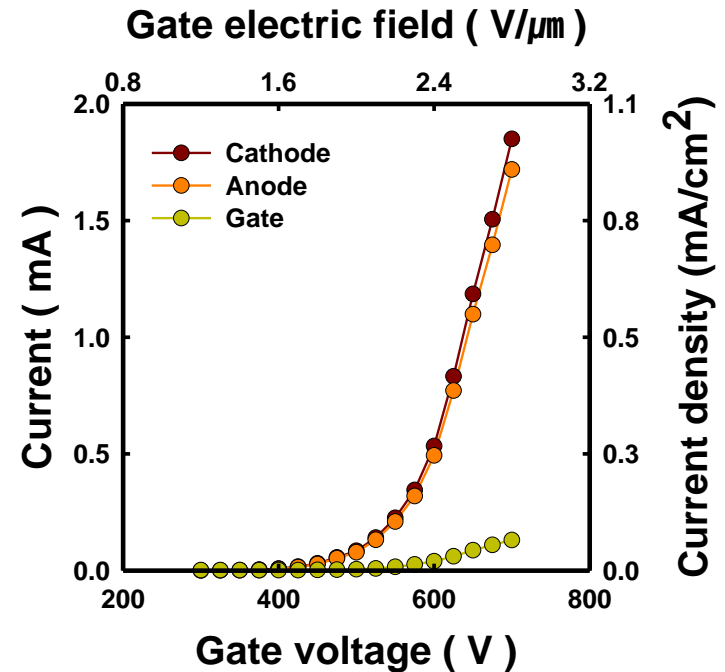
Previous works

- Specifications of C-beam for EUV lighting

- Carbon nanotube (CNT)-based cold cathode electron beam (C-beam) was manufactured for EUV lighting.



SEM image of CNT emitters

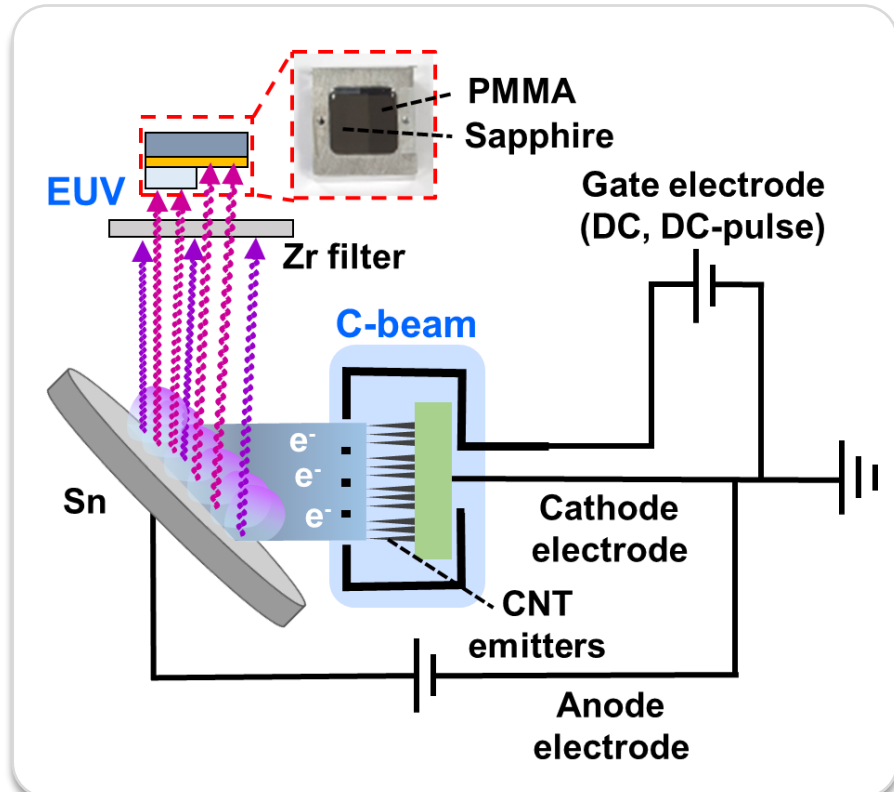


I-V characteristics of C-beam

C-beam			CNT emitters	
Anode voltage	Anode current	Gate transmittance	Height of emitters	Dot size of emitters
15 kV	0.4 mA	> 90%	40 μm	3 μm

Previous works

- EUV lithography using PMMA photoresist



Schematic of EUV lithography with C-beam

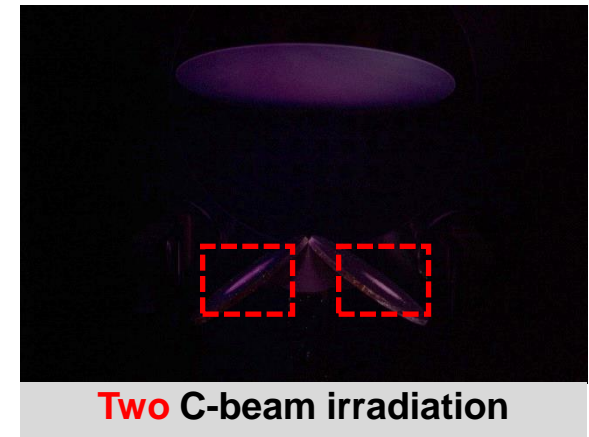
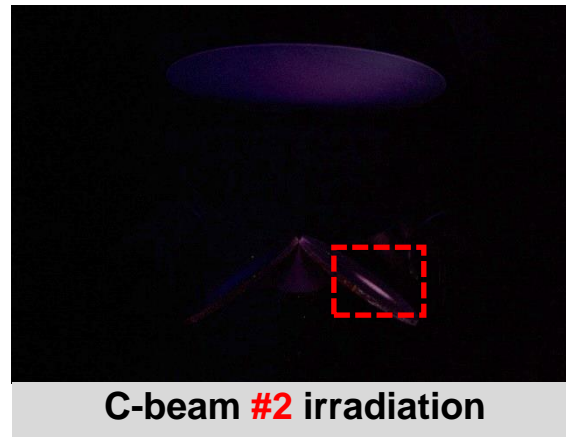
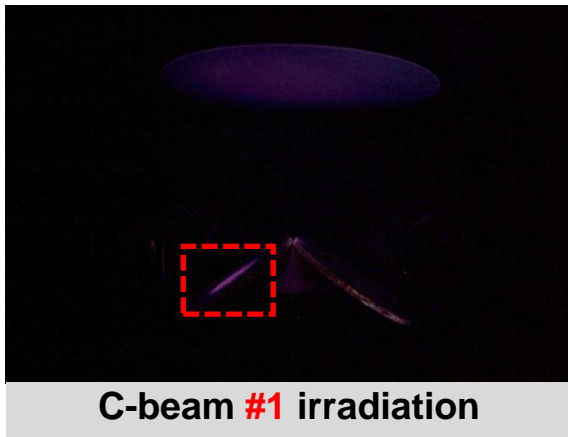
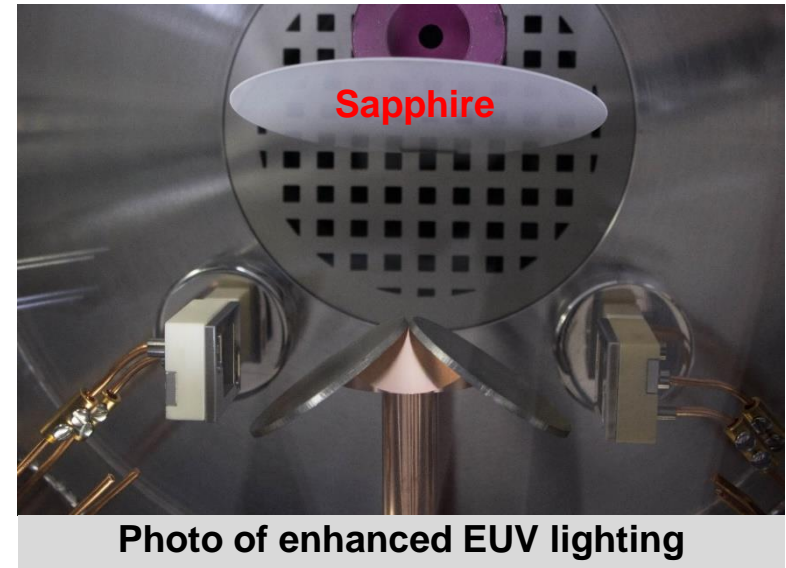
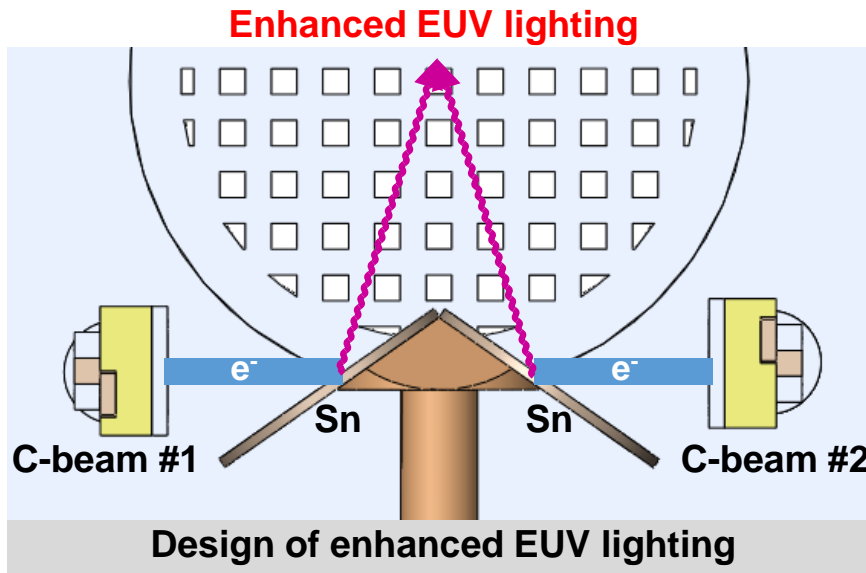


Optical microscope image after exposure and develop (Mag. x500)

- After EUV exposure and develop, the part covered by the sapphire and the part not covered by the sapphire can be accurately distinguished.
- Lithography using EUV is possible by exposing for 30 seconds at a photocurrent of $4 \mu\text{A}$ measured with a photodiode.

Enhanced EUV lighting with C-beam

- Two C-beam irradiations



※ One C-beam: 15 kV, 0.5 mA

- It was confirmed that EUV intensity is enhanced through two C-beam using EUV-PL

Enhanced EUV lighting with C-beam

- Increased photocurrent according to # of C-beams

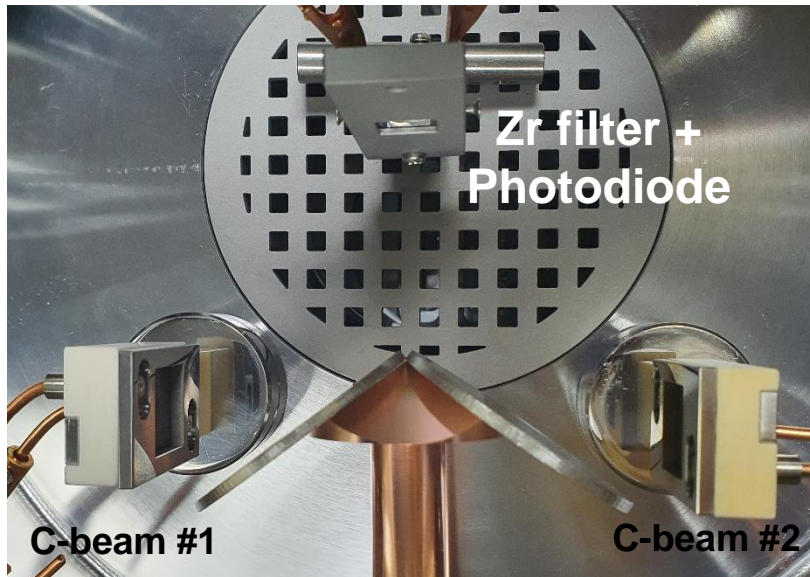
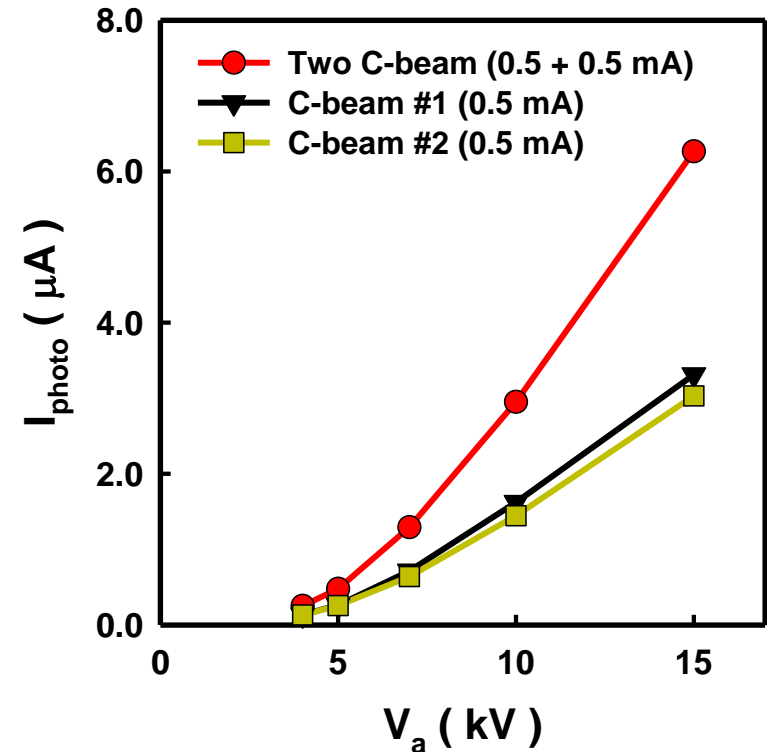


Photo of enhanced EUV lighting

DC, $V_{photo} = -1$ V, $I_a = 0.5$ mA (@ 1 C-beam)



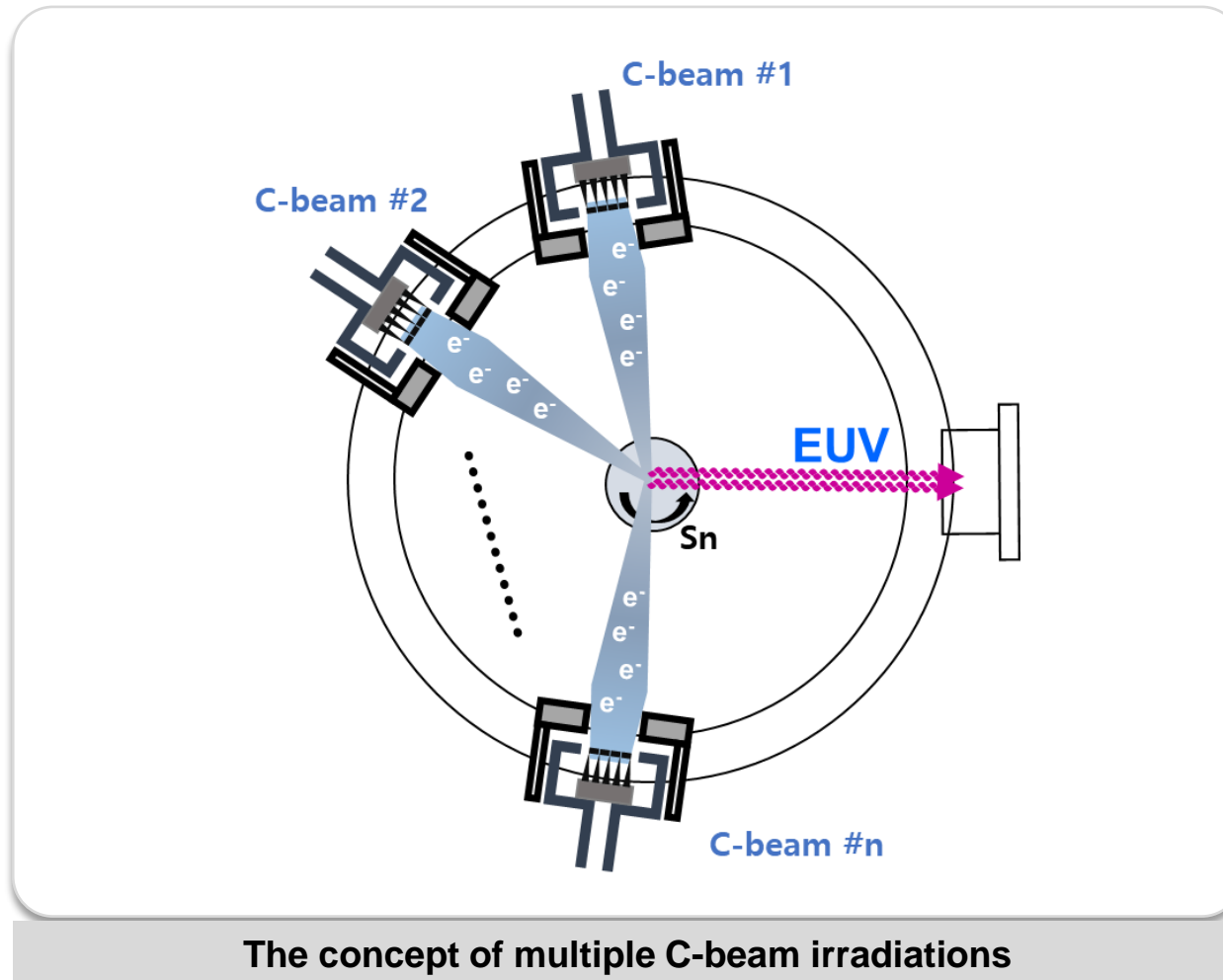
Photodiode response

- Photocurrent is doubled when using two C-beams compared to when using one C-beam.
- EUV intensity is proportional to the number of C-beams.

$$I_{photo} = 2 \times (I_{photo} \text{ of one C-beam})$$

Enhanced EUV lighting with C-beam

- The concept of multiple C-beam irradiations

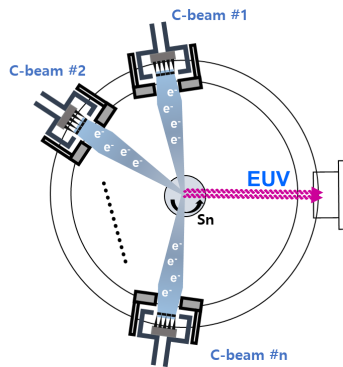


- Enhanced EUV lighting can be produced with multiple C-beam irradiations.

$$I_{photo} = (\# \text{ of } C - \text{beams}) \times (I_{photo} \text{ of one } C - \text{beam})$$



Two C-beam irradiation



The concept of multiple C-beam irradiations

- Lithography with polymethyl methacrylate (PMMA) can be performed using EUV (photocurrent of $4 \mu\text{A}$ measured with a photodiode) generated by directly irradiating electrons emitted from C-beam to Sn.
- Through two C-beam irradiations, it was confirmed that the EUV intensity is proportional to the number of C-beams.
- Enhanced EUV lighting through multiple C-beam irradiations will be applied to EUV lithography.